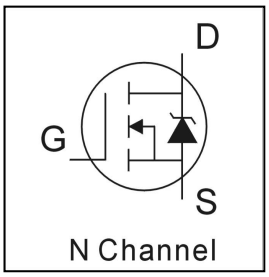
Gunter Semiconductor GmbH | GFCC30

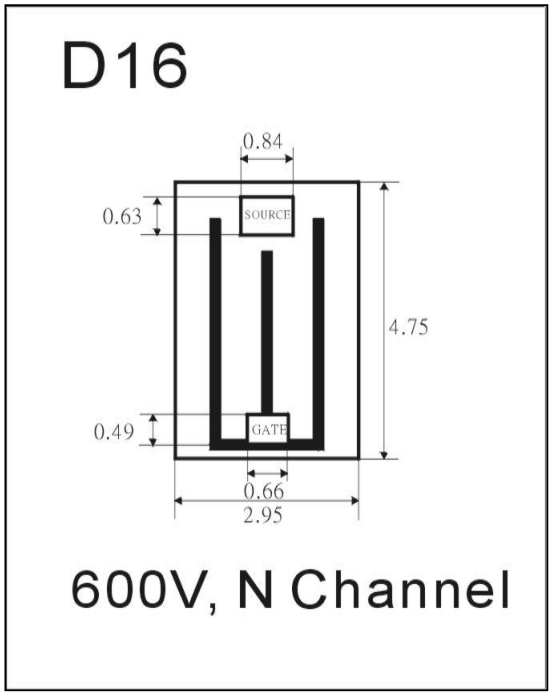
N Channel Power MOSFET with low $R_{DS(on)}$

Chip Specification



General Description:

* Advanced Process Technology
* Dynamic dV/dt Rating
* **150℃ Operating Temperature**
* **Fast Switching**
* **Fully Avalanche Rated**
* **Low $R_{DS(on)}$**



Mechanical Data:

D16	
Dimension	**2.95mm x 4.75mm**
Thickness:	**400 μm**
Metallization**:**	
Top :	: **Al**
Backside :	**CrNiAg / Au**
Suggested Bonding Conditions:	
Die Mounting:	**Solder Perform**
95/5 PbSn or 92.5./2.5/5 PbAgIn	
Source Bonding Wire**:**	**8 mil Al**

Absolute Maximum Rating @Ta=25℃

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	600	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	2.2	Ω	VGS=10V, ID=2.2A
Continuous Drain current (in target package)	ID@25℃	27	A	VGS=10V
Continuous Drain current (in target package)	ID@100℃	19	A	VGS=10V
Operation Junction	Tj	-55~150	℃	
Storage Temperature	TSTR	-55~150	℃	

Target Device: IRFBC30

TO-220AB	PD	74	W	@Tc=25℃